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ACCEPTED MANUSCRIPT

New n-type Molecular Semiconductor - Doped Insulator (MSDI) heterojunctions combining a triphenodioxazine (TPDO) and the lutetium bisphthalocyanine (LuPc₂) for ammonia sensing

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Abstract

Molecular Semiconductor – Doped Insulator (MSDI) heterojunctions were designed using a new family of sublayers, namely triphenodioxazines (TPDO). The device obtained by combining the tetracyano triphenodioxazine bearing two triisopropylsilylethynyl moieties as a sublayer with the lutetium bisphthalocyanine (LuPc₂) as a top layer showed a nonlinear current-voltage characteristic independent of the sign of the polarization, which is the signature of MSDI heterojunctions. Thus, a TPDO was used in a chemical sensor for the first time. Despite LuPc₂ being the only material exposed to the atmosphere, the positive response of the device under ammonia revealed the key role played by the n-type TPDO sublayer. The device exhibits a response stable over time and can operate in a broad range of relative humidity.

Keywords: Triphenodioxazine; Molecular materials; Heterojunctions; Conductometric transducer; Ammonia

1. Introduction

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